

IN THE CLAIMS:

1. (Currently Amended) A semiconductor laser comprising:
an n-type clad layer;
a p-type clad layer;
an active layer sandwiched by said n-type clad layer and said p-type clad layer;
and

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a current constriction layer for current confinement and light confinement
consisting of at least two layers which is disposed in either of said n-type clad layer and
said p-type clad layer,

wherein a first layer of said current constriction layer closer to said active layer
has a different conductivity type from a conductivity type of either of said clad layers in
which said current constriction layer is provided and is made of a material having almost
the same refractive index as said clad layer, which the refractive index is of said first
layer being smaller than that of said active layer, and

wherein a second layer of said current constriction layer farther from said active
layer is made of a material having a smaller refractive index than said first layer.

2. (Original) The semiconductor laser of claim 1, wherein said first layer of said
current constriction layer is formed to function mainly as a current confinement layer
and said second layer thereof is formed to function mainly as a light confinement layer
and a width of a stripe trench for injecting current provided in said first layer is smaller
than a width of a stripe trench provided in said second layer.

3. (Previously Amended) The semiconductor laser of claim 2, wherein said stripe
trench is formed so as to have an inclined surface with respect to a width-direction of

said current constriction layer, so that a width of said stripe trench for injecting current provided in said first layer is smaller than a width of said stripe trench provided in said second layer.

4. (Original) The semiconductor laser of claim 3, wherein said inclined surface of said first layer has a smaller inclination angle than said second layer.

5. (Previously Amended) The semiconductor laser of claim 2, wherein said stripe trench in said first layer and said stripe trench in said second layer are provided in different steps, so that the width of said stripe trench provided in said first layer is smaller than the width of said stripe trench provided in said second layer.

6. (Withdrawn).

7. (Withdrawn).

8. (Withdrawn).

9. (Withdrawn).